

[ABSTRACT]

COATING LIQUID FOR FORMING N-TYPE OXIDE

SEMICONDUCTOR FILM, METHOD FOR PRODUCING N-TYPE

OXIDE SEMICONDUCTOR FILM, AND METHOD FOR PRODUCING

5 FIELD-EFFECT TRANSISTOR

A coating liquid for forming an n-type oxide semiconductor film, the
coating liquid including: a Group A element, which is at least one selected
from the group consisting of Sc, Y, Ln, B, Al, and Ga; a Group B element,
which is at least one of In and Tl; a Group C element, which is at least one
10 selected from the group consisting of Group 4 elements, Group 5 elements,
Group 6 elements, Group 7 elements, Group 8 elements, Group 9 elements,
Group 10 elements, Group 14 elements, Group 15 elements, and Group 16
elements; and a solvent.

(Fig.1)